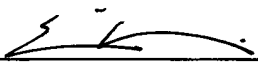


REMARKS

Further to the Amendment filed on May 20, 2002, Applicants amend claims 10, 19, 20 and 25 to correct minor typographical errors.

Should the Examiner believe that anything further would be desirable to place this application in better condition for allowance, the Examiner is invited to contact Applicant's undersigned attorney at the telephone number listed below.

Respectfully submitted,



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MARKED-UP VERSION OF THE CLAIMS

IN THE CLAIMS:

Please amend claims 10, 19, 20 and 25 as follows:

10. (Amended) A method according to claim 7, wherein said crystallization promoting material is selected [form] from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, [OS] Os, Ir, Pt, Cu and Au.

19. (Amended) A method according to claim 15, wherein said crystallization promoting material is selected [form] from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, [OS] Os, Ir, Pt, Cu and Au.

20. (Twice Amended) A method for manufacturing a semiconductor device comprising the steps of:

forming a semiconductor film on an insulating surface;

providing a crystallization promoting material onto said semiconductor film;

crystallizing [aid] said semiconductor film by a first heating;

forming a semiconductor island having a tapered shape by patterning said semiconductor film, said tapered shape having an angle within a range of 20° to 50° between a side thereof and an underlying surface; and

reducing said crystallization promoting material existing within said semiconductor island by a second heating,

wherein irradiation of laser light is performed after forming said semiconductor film.

25. (Amended) A method according to claim 22, wherein said crystallization promoting material is selected [form] from the group consisting of Fe, Co, Ni, Ru, Rh, Pd, [OS] Os, Ir, Pt, Cu and Au.